

Product Overview

FFP08S60SN: 8A, 600V, STEALTH™ II Diode

For complete documentation, see the data sheet.

The FFP08S60SN is a STEALTH™ II diode with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Features

- Stealth recovery $T_{rr} = 25\text{ns}$ (@ $I_F = 8\text{A}$)
- Max Forward Voltage, $V_F = 3.4\text{V}$ (@ $T_C = 25^\circ\text{C}$)
- 600V Reverse Voltage and High Reliability
- Improved dv/dt capability
- RoHS compliant

Applications

- LCD TV

Part Electrical Specifications

| Product | Pricing (\$/Unit) | Compliance | Status | Type | $I_{O(\text{rec})}$ Max (A) | t_{rr} Max (ns) | V_{RRM} Max (V) | V_{FM} Max (V) | I_{FSM} Max (A) | I_R Max (mA) | Package Type |
|--------------|-------------------|--|--------|--------|-----------------------------|-------------------|-------------------|------------------|-------------------|----------------|--------------|
| FFP08S60SNTU | 0.4423 | Pb-free Halide free non AEC-Q and PPAP | Active | Single | 8 | 25 | 600 | 3.4 | 60 | 0.1 | TO-220-2 |

For more information please contact your local sales support at www.onsemi.com.

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